

TOSHIBA**2SC2216, 2SC2717**

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC2216, 2SC2717

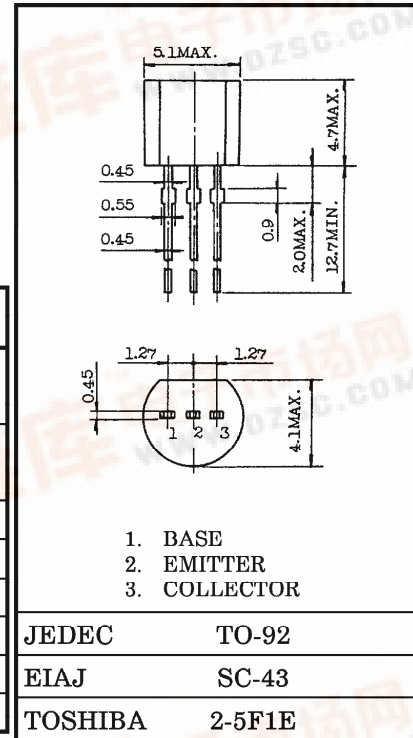
TV FINAL PICTURE IF AMPLIFIER APPLICATIONS.

Unit in mm

- High Gain : $G_{pe} = 33\text{dB}$ (Typ.) ($f = 45\text{MHz}$)
- Good Linearity of h_{FE} .

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	2SC2216	V_{CB0}	50	V
	2SC2717		30	
Collector-Emitter Voltage	2SC2216	V_{CEO}	45	V
	2SC2717		25	
Emitter-Base Voltage		V_{EBO}	4	V
Collector Current		I_C	50	mA
Emitter Current		I_E	-50	mA
Collector Power Dissipation		P_C	300	mW
Junction Temperature		T_j	125	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55~125	$^\circ\text{C}$



Weight : 0.21g

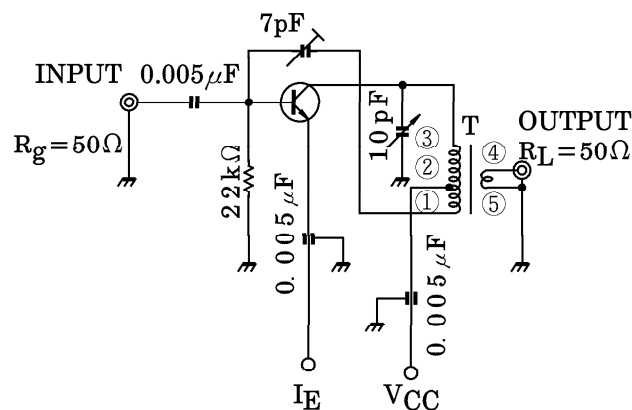
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	2SC2216	I_{CBO}	$V_{CB} = 50\text{V}, I_E = 0$	—	—	0.1	μA
	2SC2717		$V_{CB} = 30\text{V}, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 3\text{V}, I_C = 0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	2SC2216	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	45	—	—	V
	2SC2717			25	—	—	
DC Current Gain	2SC2216	h_{FE}	$V_{CE} = 12.5\text{V}, I_C = 12.5\text{mA}$	40	—	140	—
	2SC2717			40	—	240	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 15\text{mA}, I_B = 1.5\text{mA}$	—	—	0.2	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 15\text{mA}, I_B = 1.5\text{mA}$	—	—	1.5	V
Collector Output Capacitance		C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 30\text{MHz}$	0.8	—	2.0	pF
Collector-Base Time Constant		$C_c\text{-rbb'}$	$V_{CB} = 10\text{V}, I_E = -1\text{mA}, f = 30\text{MHz}$	—	—	25	ps
Transition Frequency		f_T	$V_{CE} = 12.5\text{V}, I_C = 12.5\text{mA}$	300	—	—	MHz
Power Gain (Fig.)	2SC2216	G_{pe}	$V_{CC} = 12.5\text{V}, I_E = -12.5\text{mA}, f = 45\text{MHz}$	29	—	36	dB
	2SC2717			28	—	36	

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● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.





COIL DATA
0.20mm ϕ Cu WIRE
L=1.2 μ H WITH M-5 CORE
T : ①-② 3.0T
②-③ 8.0T
④-⑤ 1.0T

STATIC CHARACTERISTICS

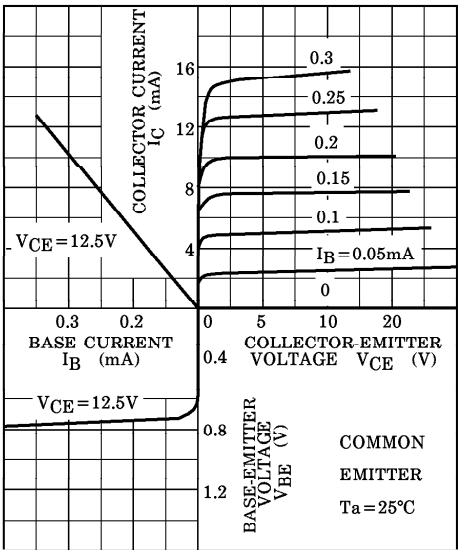


Fig. 45MHz G_{pe} TEST CIRCUIT

